

Quantum Diffusion

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Basic ideas and results which characterize quantum diffusion of defects in quantum crystals like solid helium as a new phenomenon are presented. Quantum effects in such media lead to a delocalization of point defects (vacancies, impurities etc.) and they turn into quasiparticles of a new type — defectons, which are characterized not by their position in the crystal lattice but by their quasimomentum and dispersion law. Defecton-defecton and defecton-phonon scattering are considered and an interpolation formula for the diffusion coefficient valid in all interesting temperature and concentration regions is presented. A comparison with the experimental data is made. Some alternative points of view are discussed in detail and the inconsistency of the Kisvarsanyi-Sullivan theory is shown.

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I. INTRODUCTION

The basic characteristic of a quantum crystal is the presence of a large amplitude of atomic zero-point vibrations. This means that the overlap of the wave functions of the nearest neighbours is not negligible and leads to considerable tunnelling transitions to the nearest lattice sites. If a point defect (vacancy, impurity, interstitial) appears in such a system, the crystal state becomes degenerate with respect to the defect position due to the identity of lattice sites and the defect delocalizes and turns into a quasiparticle - *defecton*. If the wave function of the crystal with a localized defect in the lattice site $\mathbf{r}$ is $\psi_{\mathbf{r}}(x)$, then the right wave function of the crystal, according to the Bloch theorem, is [1]

$$\Psi_{\mathbf{k}} = \frac{1}{\sqrt{N}} \sum_{\mathbf{r}} \psi_{\mathbf{r}}(x) \exp\{i(\mathbf{k}\mathbf{r} - \epsilon(\mathbf{k})t/\hbar)\} \quad (1)$$

where x is a $3N$ component vector which consists of all atomic coordinates, and $\mathbf{k}$ is the defecton quasiwavevector. The spectrum is given by the defecton dispersion law $\epsilon(\mathbf{k})$. In a tight binding approximation it has the form

$$\epsilon(\mathbf{k}) = \Phi + A\omega(\mathbf{k}) \quad (2)$$

where Φ is the activation energy of a localized defect, A is the tunnelling probability amplitude (exchange integral), and $\omega(\mathbf{k})$ is a dimensionless function which depends on the symmetry of the crystal lattice. For a simple cubic lattice the dispersion law is of the form

$$\epsilon(\mathbf{k}) = \Phi + A(\cos k_x a + \cos k_y a + \cos k_z a) \quad (3)$$

and for body-centered cubic lattice (b.c.c.)

$$\epsilon(\mathbf{k}) = \Phi + 4A \cos \frac{k_x a}{2} \cos \frac{k_y a}{2} \cos \frac{k_z a}{2} \quad (4)$$

where a is the lattice constant. For defects in solid helium, the quantity Φ is of the order of several degrees. In case of h.c.p. lattice, there are two atoms per unit cell

and the dispersion law consists of two branches called conditionally *acoustic* and *optical* respectively [2, 3, 4]:

$$\epsilon(\mathbf{k})_{\frac{ac}{opt}} = \epsilon_0 + A \left\{ 7 - 4 \cos \frac{\mathbf{k}_1 \cdot \mathbf{a}_1}{2} \cos \frac{\mathbf{k}_2 \cdot \mathbf{a}_2}{2} \cos \frac{\mathbf{k}_3 \cdot \mathbf{a}_3}{2} \mp \cos \frac{\mathbf{k} \cdot \mathbf{c}}{2} \left[1 + 8 \cos \frac{\mathbf{k}_1 \cdot \mathbf{a}_1}{2} \cos \frac{\mathbf{k}_2 \cdot \mathbf{a}_2}{2} \cos \frac{\mathbf{k}_3 \cdot \mathbf{a}_3}{2} \right]^{1/2} \right\} \quad (5)$$

where

$$\mathbf{a}_1 = a[1, 0, 0], \mathbf{a}_{2,3} = a \left[-\frac{1}{2}, \pm \frac{\sqrt{3}}{2}, 0 \right], \mathbf{c} = a \left[0, 0, \frac{\sqrt{8}}{3} \right]. \quad (6)$$

An important characteristic of a defecton is its energy band width Δ . For simple lattices $\Delta = zA$, where z is the number of nearest neighbours in the lattice. For the h.c.p. lattice, the dispersion law (5) is written in a form which fixes the bottom of the acoustic band at $k = 0$, so that $\epsilon(0) = \epsilon_0$ is the lowest band level. The band width of the acoustic branch is $\Delta_{ac} = 7A$ while that of the optical one it is $\Delta_{opt} = 5A$. The bottom of the optical branch lies higher by $3A$. A typical value of Δ for ^3He impurities in ^4He is $\Delta \sim 10^{-4}K$, while for vacancies Δ is of the order of several degrees. The defecton velocity is $\mathbf{v} = \frac{1}{\hbar} \frac{\partial \epsilon}{\partial \mathbf{k}}$ and may be estimated by the relation $v \sim a\Delta/\hbar$. The effective mass for simple lattices is $m^* = \hbar^2/Aa^2$ while for the h.c.p. dispersion law (5) one has $m_{hcp}^* = \hbar^2/2Aa^2$. Another important quantity is the delocalization time τ_0 which may be estimated by the relation [2, 5]

$$\tau_0 \sim A/\hbar. \quad (7)$$

Note, that in this relation the characteristic energy is the exchange integral A , not the band width Δ .

Before going on with defecton diffusion let us note that there are crystals in which zero-point vibrations are large only for certain degrees of freedom and hence the quantum properties manifest themselves with respect to them. The class of quantum crystals includes therefore heavy

metals (palladium, niobium etc.) in which the behaviour of light hydrogen impurities (protons) is quantum, solid hydrogen with impurities of hydrogen atoms, metallic hydrogen, etc.

From a historical point of view, however, physics of quantum crystals is above all bound up with solid helium. Helium has been chosen for a basic system when examining the ideas and results of the theory owing to a number of circumstances. Solid helium is the best investigated quantum crystal. Helium crystals are extremely pure – all other elements solidify at higher temperatures, so the only impurities are isotopes and can be well controlled in wide concentration ranges. The two helium isotopes obey two quantum statistics – those of Bose-Einstein and Fermi-Dirac. In addition, each isotope crystallizes in three different modifications. In such a way *solid helium offers six quantum crystals, composed of two isotopes only*. Phase diagrams for helium isotopes can be found, e.g. in [6, 7, 8].

Any correct theoretical model has to include not only a description of the structure and building particles, but also the typical kinds of motion in it, or, in other words, *the elementary excitations as elementary carriers of the motions*. In this sense crystals of solid ^4He with small concentrations of isotopic impurities and vacancies may serve as examples of really existing model systems, in which the only elementary excitations are phonons and defectons. In addition, the low value of the melting temperature compared to the Debye temperature leads to a simple linear dispersion law for phonons in the whole range of existence of the solid phase. It is worth noting that the new (tunnel) kind of motion presented by the defecton quasiparticles is the reason to call the state of quantum crystals the *a new state of the matter*.

For ^3He atoms which have spin equal to $1/2$ and relatively large magnetic moment an exchange of atoms is equivalent to a spin exchange (the interatomic potential practically does not depend on spin) and therefore may be observed experimentally, e.g. by means of nuclear magnetic resonance (NMR) [9].

The presence of two types of crystals composed of Fermi- and Bose- atoms puts forward the problem of defecton statistics. It can be shown that in pure crystals with small defect concentration vacancies obey the statistics of host atoms. Impurities of ^3He in crystals of ^4He as well as impurities of ^4He in crystals of ^3He turn into Fermi-quasiparticles. In case of mixed crystals a vacancy has to exchange places with different atoms (^3He or ^4He) that obey different statistics, therefore, the vacancy statistics can differ from the known statistics of Bose-Einstein or Fermi-Dirac. More information on defecton statistics can be found elsewhere [2, 10]. The degeneracy temperature T_0 is extremely small:

$$T_0 \sim \Delta x^{2/3} \quad (8)$$

where x is the fractional concentration of defects. For vacancies with a typical concentration $x \sim 10^{-3}$ the degeneracy temperature is $T_0 \sim 10^{-2} - 10^{-3}\text{K}$. That

is why in many cases defectons may be considered as a Boltzmann gas. It is important to note, however, that the role of statistics increases with decreasing concentration. Indeed, the interaction energy E_{int} between point defects in solids is inversely proportional to the third power of the spacing r and hence is proportional to the concentration x :

$$E_{int} = \frac{V_0 a^3}{r^3} = V_0 x \quad (9)$$

where V_0 is the elastic interaction constant which typical value is of the order of 10^{-2}K . Taking into account (8), one obtains

$$\frac{T_0}{E_{int}} \sim \frac{\Delta}{V_0} x^{-1/3}. \quad (10)$$

Therefore, at low enough concentrations the interaction energy E turns out to be negligible compared to the "quantum statistics energy" T_0 . The critical concentration for a gas of vacancies is $\sim 10^{-1}$ and is much greater than the usual vacancy concentration in the experiments.

II. HISTORICAL REVIEW

A phenomenological theory of defects in quantum crystals was proposed first by A.F.Andreev and I.M.Lifshitz [11] in 1969. The qualitative estimations concerning diffusion in that work differ from the quantitative ones more than 7 orders of magnitude and are only of historical interest now. Simultaneously, the author of this work reported at the Second Soviet Conference on Theory of Solid State in Moscow his microscopic theory of vacancies and impuritons (published as a paper [1] in 1970) where the defecton parameters were estimated and the temperature dependence of the defecton mean free path was obtained.

At the same time Guyer and Zane [12] published their perturbation theory of the spectrum of impuritons (called *mass-fluctuation waves*) and showed the possibility of experimental observation by the method of nuclear magnetic resonance.

It is worth noting that there was a significant interest in quantum crystals at those years but there were no experimental evidences on quantum diffusion. Moreover, some results on the diffusion of point defects [13, 14] were considered as arguments in favour of the classical activation mechanism. There was not any clear conception of the correlation between the quantum and classical weights in the phenomena considered. This prevented often even the correct formulation of the problems. Instructive in this aspect is the work of C.P.Flynn and A.M.Stoneham [15] on the diffusion of light interstitials. The authors have practically neglected the coherent quantum diffusion stressing the role of phonons and deformation around the defect. This was a result of their conception that the incoherent (by means of phonons) transition corresponded to a macroscopic

number of channels, while the coherent tunnelling corresponded to one. In this way, an implausible estimation has been made for the temperature region in which coherent diffusion could be observed, given by the inequality $T \leq 10^{-17}K$.

The assumption that defects turn into quasiparticles means that (at some conditions considered later on) the gas kinetic model is applicable and hence the diffusion coefficient has to be inversely proportional to the concentration, i.e.

$$D \sim Aa^2/\hbar x\sigma \quad (11)$$

where σ is the defecton-defecton cross-section (in units a^2). The temperature dependence predicted [16, 17] was of the form

$$D_T \sim as \left(\frac{\Delta}{\theta_p}\right)^2 \left(\frac{\theta_p}{T}\right)^9, \quad \theta_p = \frac{\hbar s}{2a}. \quad (12)$$

The ninth power of temperature is easy to understand (for details see Refs. 1, 18). The motion of a defect is determined by the number of phonons ($N_{ph} \sim T^3$ at low temperatures) and, by the scattering of long wave phonons on defects (Rayleigh scattering) with a cross-section $\sigma \sim k^4 \sim T^4$; finally, the motion of a "heavy and slow" defecton in a gas of "light" phonons depends on the second power of the phonon wave vector ($\sim k^2 \sim T^2$). Hence, $D \sim 1/(N_{ph}\sigma T^2) \sim T^{-9}$. It is worth noting that the role of the characteristic temperature is played by θ_p , not by the Debye temperature θ_D . These two temperatures differ significantly: $\theta_p = \frac{\hbar s}{2a} \approx \frac{\theta_D}{8}$ and lead to a numerical difference of the order of $8^7 \sim 10^6$ times.

It could be expected that such a rapid increase of the diffusion with decreasing temperature can easily be observed experimentally. However, the experiments on both vacancy [13] and impurity [19] diffusion carried out in ^4He with $0.75 \div 2\%$ impurity concentration indicated typical classical exponential decreasing down to the phase separation temperature.

The first evidence of a quasiparticle behaviour was reported by R.G.Richards, J.Pope and A.Widom [20]. They confirmed the concentration dependence $\sim 1/x$. However for the tunnelling frequency A they obtained the value $A \sim 10^{-7}K$, which is three orders of magnitude smaller than the exchange integral J_{33} in pure ^3He . The interpretation of such a value ran into difficulties because there were no physical reasons for such dramatic difference in the exchange integrals. It became clear that additional information is necessary and that it could be obtained from the temperature dependence (12). An increasing diffusion with decreasing temperature was first observed by the Kharkov group [21, 22] in 1973. Surprisingly, the treatment of the experimental data using the theory of Andreev and Lifshitz [11] gave for the exchange integral A a value of the same order of magnitude as that obtained in [20].

The plain model of free quasiparticles became questionable and in 1974 Landesman and Winter [23] and later on Huang et al. [24] proposed an alternative model leading to another concentration dependence:

$$D \sim \frac{Ja^2}{\hbar x^{4/3}}, \quad J = \frac{J'^2}{K} \quad (13)$$

where J' is the exchange integral in the pure crystal, and K is a phenomenological parameter describing the repulsion of two atoms in one lattice site.

The authors argued that this dependence is valid for concentrations $x > 10^{-6}$, i.e. in the whole experimentally accessible region. Unfortunately, the experimental precision was not enough to distinguish the small difference between the concentration dependencies in (11) and (13), especially taking into account that both A and J were unknown.

In order to solve the paradox the author treated the experimental data of the Kharkov group using his theory [17]. As a result, the exchange integral A was found to be only slightly smaller than J_{33} , the band width was estimated to be $\Delta \sim 10^{-4}K$ and the prediction of the giant defecton-defecton cross-sections in [1] was confirmed. The existence of the new quasiparticles (defectons) became an immutable fact and the discovery of a new phenomenon called *quantum diffusion* was acknowledged.

III. DEFECTON-DEFECTON SCATTERING

The only scattering processes which determine the defecton diffusion are collisions with defectons and phonons. If the temperature is small enough (the exact conditions will be derived below) the number of phonons is negligible, and the defecton free path is controlled by defecton-defecton interaction.

Defecton-defecton scattering possesses a series of peculiarities relevant to the energy band width [1, 2, 17, 18]. First of all, the quasiparticle energy cannot vary during the motion more than the energy band width Δ . This means that the quasiparticle is not able to overcome barriers higher than Δ . In case of impuritons in helium, a typical value of the deformation energy caused by a vacancy or impurity is of the order of $10^{-2}K$ and is much larger than $\Delta_{imp} \sim 10^{-4}K$. As a result, the quasiparticle cannot reach the core of the vacancy (or interstitial) and exchange place with it (the later case of vacancy-stimulated diffusion has been discussed in Sec. VII). This is important because the exact form of the deformation in the core is complicated and not known, while the behaviour of the deformation field at large distances is common for wide classes of solid media. The later allows to study the defecton scattering in a quite general form.

Point defects in crystals interact by the law

$$\varphi(\mathbf{r}) = V_0\Gamma(\mathbf{n}) \left(\frac{a}{r}\right)^3, \quad (14)$$

where $\Gamma(\mathbf{n})$ is a function of the direction $\mathbf{n}$, which vanishes after angle averaging and is of the order of unity. In an isotropic media

$$\varphi(r) = V_0 \left(\frac{a}{r} \right)^6. \quad (15)$$

Let us consider first the features of the defecton scattering in a potential of a more general form:

$$\varphi(r) = V_0 \left(\frac{a}{r} \right)^n. \quad (16)$$

The small value of the impuriton energy band width leads to a peculiar confinement in areas with strong field gradients. This effect takes place both in attractive and in repulsive potentials. Its physical reason is that the transition of the quasiparticle into a neighbouring lattice site cannot take more energy than the band width. Therefore, the condition for such a confinement may be written in the form

$$|\nabla\varphi| a > \Delta. \quad (17)$$

Substituting here φ from (16) and replacing the mean distance r between defects by their concentration $x \approx (a/r)^3$ one obtains that all defects has to be localized [11] at concentrations $x > x_c$, where

$$x_c = \left(\frac{\Delta}{nV_0} \right)^{\frac{3}{1+n}}. \quad (18)$$

In the case of isotopic impurities in helium ($n = 3$) the quantity x_c is

$$x_c = \left(\frac{\Delta}{3V_0} \right)^{\frac{3}{4}} \approx 1 \div 2\%. \quad (19)$$

Due to the small value of the defecton band width large regions around the impurities are unscalable for quasiparticles [1, 18]. Their linear size R_0 may be estimated from the equation

$$\varphi(R_0) = \Delta, \quad R_0 = a \left(\frac{V_0}{\Delta} \right)^{1/n}. \quad (20)$$

Hence, the effective cross-section σ for impuritons in the potential (16) is

$$\sigma \approx \pi a^2 \left(\frac{V_0}{\Delta} \right)^{2/n}. \quad (21)$$

These estimations may be improved taking into account, that the experiments are performed at temperature $T \gg \Delta$ and, therefore, the conditions for the quasi-classical approximation are satisfied:

$$(ka)^{n-2} \gg \frac{A}{V_0} \approx \frac{\Delta}{zV_0}. \quad (22)$$

In this case the cross-section is given by the expression [1]:

$$\sigma \approx 2\pi a^2 \left(\frac{V_0}{Aka} \right)^{\frac{2}{n-1}} \sim \pi a^2 \left(\frac{V_0}{\Delta} \right)^{\frac{2}{n-1}}. \quad (23)$$

(States with $ka \gtrsim 1$ are activated due to the high temperature).

In the most interesting case, when $n = 3$, the cross-section

$$\sigma \sim \pi a^2 \frac{V_0}{\Delta} \quad (24)$$

can reach giant values $\sigma \sim 10^2 a^2$. Eq. (23) shows that the effective cross-section in the gas approximation (*noninteracting* quasiparticles) considered is inversely proportional to the band width Δ . The same dependence on Δ follows also from the theories of Landesman [25] and Yamashita [26] for *interacting* quasiparticles. This coincidence is evidently the explanation of the fact that the dependence of the diffusion coefficient on the molar volume ("the Grüneisen parameter") does not vary with decreasing concentration [27] (see below).

The condition (22) can be satisfied at lower temperatures as well if the following inequalities take place

$$A(A/V_0)^{\frac{2}{n+1}} \ll T \ll \Delta \quad (25)$$

Then the quasiparticle thermal energy may be evaluated from the relation $\hbar^2 k^2 / 2m^* \approx 3T/2$. With $m^* \approx \hbar^2 / Aa^2$ this yields $ka \sim (T/A)^{1/2}$, and the cross-section (23) can be written in the form

$$\sigma \approx \pi a^2 \left(\frac{V_0^2}{TA} \right)^{\frac{1}{n-1}} \underset{n=3}{=} \pi a^2 \frac{V_0}{\sqrt{TA}}. \quad (26)$$

It increases with decreasing temperature up to the value

$$\sigma_{max} \approx \pi a^2 (V_0/A)^{\frac{2}{n-2}} \underset{n=3}{=} \pi a^2 (V_0/A)^2. \quad (27)$$

The opposite situation which corresponds to the scattering of a slow particle by a rapidly decreasing potential barrier ($n = 6$) can take place for vacancies at $T \ll \Delta$. Then the cross-section does not depend on velocity, and hence, is independent of temperature:

$$\sigma \approx 3.65\pi a^2 \left(\frac{V_0}{2A} \right)^{\frac{1}{2}}. \quad (28)$$

This expression fits well to that of Eq. (27) at $n = 6$. If vacancy-vacancy scattering is under consideration, then $V_0 \sim ms^2$, $A = 1K$, and hence, $\sigma = 50a^2$.

In the consideration above we did not take into account the role of the anisotropy given by the factor $\Gamma(\mathbf{n})$ in the potential (14). It is obvious that such a sign-variable function with zero averaged value can only reduce the cross-section. According to Slusarev et al. [28]

the anisotropy reduces the total cross-section by a factor 0,105 (cubic lattices), and 0,208 (h.c.p. crystals). The reduction for the transport cross-section is about 4-5 times. However, the exchange integral A as well the defecton band width Δ evaluated in the same work turned out to be more than an order of magnitude less compared to the results adopted now.

Situations where $\Delta \gg V_0$ are realized in vacancion scattering by isotopic impurities. In such cases Born approximation may be used and the problem can fully be solved in an analytical form with an account of the exact form of the function $\Gamma(\mathbf{n})$ [16, 18]. It can be shown that the scattering amplitude $F(\mathbf{n})$ has the same angular dependence as the interaction potential: $F(\mathbf{n}) = \lambda \Gamma(\mathbf{n})$. For a simple cubic lattice $\lambda = (2a/15)(V_0/A)$, and therefore,

$$d\sigma = \frac{4}{225} a^2 (V_0/A)^2 \Gamma^2(\mathbf{n}) d\Omega, \quad (29)$$

where $\Gamma(\mathbf{n}) = \sum_i n_i^4 - 3/5$.

One has to keep in mind, however, that the interaction potential has the form (14) only at large distances and the effect of the scattering by the core needs for wide-band vacancions a special consideration.

Consider briefly the role of the defecton statistics. If defectons obey Fermi-Dirac statistics, then their quasimomenta has to be near to the value of the Fermi-quasimomentum both before and after collision. As far as the cross-section is proportional to the final states number, it is proportional to temperature T . Therefore,

$$\sigma_F = \sigma' T / \epsilon_F. \quad (30)$$

The quantity σ' for the potential (16) with $n = 3$ in quasiclassical approximation is of the form [2, 29]

$$\sigma' = 2\pi^2 \frac{V_0 a}{\hbar v_F} \quad (31)$$

where v_F is the Fermi-velocity. Therefore, the cross-section depends not only on the ratio V_0/A , but also on the concentration:

$$\sigma_F \sim T \frac{V_0}{A^2 x}, \quad T < A x^{2/3}. \quad (32)$$

The condition for the applicability of the expressions (31) and (32) follows from (22) where one must take into account, that $k_F a \sim x^{1/3}$:

$$x > (A/V_0)^3. \quad (33)$$

It is worth noting also that the ratio V_0/A is strongly dependent on pressure, and increases rapidly with decreasing molar volume.

IV. LOW TEMPERATURE DIFFUSION

Let us now turn to the diffusion. As follows from the gas kinetics theory the diffusion coefficient is equal to

$$D = \frac{1}{3} l v. \quad (34)$$

where the mean free path is

$$l = a / \sqrt{2} x \sigma \quad (35)$$

This approximation is valid if the mean distance between quasiparticles, $x^{-1/3}$, is much larger than the "radius" of the cross-section $R_0 \sim \sqrt{\sigma}$, i.e. if $x^{-1/3} \gg \sqrt{\sigma}$ or (what is the same):

$$x \ll 1/\sigma^{3/2}. \quad (36)$$

The quasiparticle mean velocity v depends, in general, on the temperature. If $T \gg \Delta$ which is the case realized in experiments on impurity diffusion in helium, then the levels till the top of the energy band are populated. Sacco and Widom [30] calculated the band-averaged value of the velocity squared in a h.c.p. lattice and obtained (in our notation)

$$v_{SW} = (\langle v^2 \rangle)^{1/2} = \frac{3}{\sqrt{2}} \frac{a_0 A}{\hbar} = \frac{3}{2\sqrt{2}} s \frac{A}{\theta_p} \approx s \frac{A}{\theta_p}. \quad (37)$$

In principle, this value can be used to estimate the order of magnitude of the diffusion coefficient (34). However, it is well known (see e.g. Ref. [31]) that the correct value of the velocity is closer to its highest value which can be evaluated from the relation $m^* v^2/2 = \Delta$:

$$v \approx s \frac{1}{\sqrt{2z}} \frac{\Delta}{\theta_p} \approx 2,45 s \frac{A}{\theta_p} \quad (z = 12). \quad (38)$$

The diffusion coefficient is therefore (comp. to (11)):

$$D_0 = \frac{1}{6\sqrt{z}} \frac{as}{x\sigma} \frac{\Delta}{\theta_p} \approx \frac{1}{\sqrt{3}} \frac{as}{x\sigma} \frac{A}{\theta_p} \quad (z = 12). \quad (39)$$

Substituting here σ from (24) yields

$$D_0 = \frac{1}{6\pi\sqrt{z}} \frac{as}{x} \frac{\Delta^2}{V_0 \theta_p} = \frac{1}{3\pi\sqrt{z}} \frac{a^2}{\hbar x} \frac{\Delta^2}{V_0}. \quad (40)$$

In order for the defectons to be good quasiparticles, their mean free path should be larger than the lattice constant, i.e. the coherency condition $x\sigma < 1$ should be satisfied. This leads to the following restriction on the defecton concentration:

$$x < x_0 \equiv \sigma^{-1}. \quad (41)$$

As we showed in the previous section the cross-sections σ can be extremely large. That is why the condition (41) is weaker than (36). Hence, the gas-kinetics formula (39) is valid for concentrations

$$x < \sigma^{-3/2} < \sigma^{-1} = x_0. \quad (42)$$

The concentration x_0 turns out to be smaller than the critical concentration x_c (19). This means that *the localization process may be considered in terms of quasiparticles*. Making use of the results obtained we may

distinguish the following concentration regions depending on the powers of the small parameter $\xi = \Delta/V_0$:

- I. $x < \xi^{3/n-1} \leq 10^{-3}$ — gas approximation
 - II. $\xi^{3/n-1} < x < (\xi/n)^{3/n+1} \sim 10^{-2}$ — interacting quasiparticles
 - III. $(\xi/n)^{3/n+1} < x$ — localized defectons
- (The numerical values are calculated for $n = 3$)

Let us consider now the diffusion in the second region. In this case the mean free path l is controlled by the *scattering on the defecton band boundaries* (Fig. ??), i.e. by the condition $l \mid \nabla\varphi \mid \approx \Delta$. This means that the variation of the defecton energy along a distance l should not exceed the band width Δ . The corresponding diffusion coefficient in this region is therefore of the form [23, 24, 32]:

$$D \sim \frac{\Delta^2}{V_0 x^{(n+1)/3}} \quad (43)$$

It is worth noting that the cross-sections both in region II, and in region I depend on Δ . This dependence is important not only for choosing suitable defect concentration and perfection of the crystal samples. The knowledge of the diffusion coefficient as a function of Δ allows to find the dependence of D on the molar volume V_m . Since this dependence is strong and different in different concentration regions, one may use it to detect a change of the scattering mechanism.

At temperatures lower than the degeneracy temperature T_0 , diffusion depends on defecton statistics [29]. If the quasiparticles obey Fermi-statistics, then the gas approximation yields

$$D_F = \frac{1}{3} l_F v_F, \quad \text{where} \quad v_F = (3\pi^2)^{1/3} \frac{Aa}{\hbar} x^{1/3} \quad (44)$$

and the mean free path is

$$l_F = \frac{a}{\sqrt{2\sigma} x_{eff}}.$$

Since only defectons near the Fermi-surface take part, the “active concentration” is equal to

$$x_{eff} = x \frac{T}{\epsilon_F}$$

and the effective cross-section is given by Eqs. (30)–(32). As a result, the mean free path and the diffusion coefficient are multiplied by an additional factor $(\epsilon_F/T)^2$. This yields

$$D_F = \frac{1}{3} \frac{a v_F}{x \sigma_0} \left(\frac{\epsilon_F}{T} \right)^2 \quad (45)$$

Taking into account (31) one may rewrite Eq. (45) in the form

$$D_F = \frac{3\pi^2}{16} a s \frac{A^4}{\theta_p V_0 T^2} x. \quad (46)$$

Of course, the increase of l_F and D_F with decreasing temperature is limited by the finite size of the sample, or by scattering on other crystal defects.

In the case of Bose-defectons the diffusion coefficient may be estimated taking into account that the “actual” concentration depends only on temperature:

$$x \approx \frac{1}{6} \left(\frac{T}{A} \right)^{3/2}$$

and hence, the mean free path is

$$l \approx \frac{6a}{\sqrt{2}\sigma} \left(\frac{A}{T} \right)^{3/2}.$$

The mean velocity is

$$v \approx 1,75 \frac{a}{\hbar} (AT)^{1/2}.$$

The diffusion coefficient is therefore

$$D \approx 1,25 \frac{a s}{\sigma} \frac{A^2}{\theta_p T}.$$

If the mean free path turns out to be larger than the sample size L , then

$$D \sim \frac{La}{\hbar} (AT)^{1/2}.$$

One has to keep in mind, however, that those effects can be violated by a superfluid current, which can take place even at small chemical potential gradient.

Apparently, the diffusion at $T < T_0$ is not observable in helium due to the rapid decreasing of vacancion concentration (except of zero-point vacancions, not found yet) and the phase separation in the case of impurities. To observe it one may have to look for another quantum system.

V. PHONON CONTROLLED DIFFUSION

At absolute zero temperature a defecton moves through a crystal like a free particle without dissipation. In view of its low velocity compared with the sound one, the gas of zero-point phonons has time to adjust itself to the defecton which moves together with an adiabatically adapted phonon “cloud” that strongly influences only its effective mass. Note, that null-phonons do not change the periodicity of the lattice.

With rising temperature, scattering of thermal phonons by the defecton sets in. Since the defecton mass is large and its lifetime is much longer than the relaxation time of the phonon gas the cross section for scattering by a defecton can be replaced in zeroth approximation with respect to the small parameter $(v/s)^2$ by the cross section for scattering by an immobile defect. As it has been shown by I.M.Lifshitz [33] (see also [34, 35]) such a problem can be solved in an analytical form [1, 2, 3].

The differential cross-section for the scattering of a phonon of the j -th mode with polarization ν as a result of which a phonon of the i -th mode with a polarization ν' is produced is given by the expression [1]:

$$d\sigma_{j\mathbf{k},i\mathbf{k}'}^{\nu\nu'} = \left(\frac{V}{4\pi m s_i^2} \right)^2 (q_i^{\nu'})^2 \times \left\{ \sum_{\mu\mu'} q_i^\mu q_j^{\mu'} \sum_{RR'} \mathbf{kR} \Lambda_{RR'}^{\mu\mu'} \mathbf{k}'\mathbf{R}' \right\}^2 d\Omega' \quad (47)$$

where V is the lattice cell volume, s_i is the sound velocity of the corresponding phonon branch, $q_j^{\nu'}$ is the polarization vector and $d\Omega' = 2\pi \sin\alpha d\alpha$, α being the angle between the directions of the incident and scattered phonons. The matrix $\Lambda_{\mathbf{R}\mathbf{R}'}^{\mu\mu'}(\mathbf{r})$ describes the change of the elasticity matrix caused by the defect (situated in the lattice site $\mathbf{r}$). Averaging over the modes and polarizations of the incident phonons and summing over the modes and polarizations of the scattered ones yield

$$d\sigma_{kk'} = \left(\frac{V}{2\pi} \right)^2 k^4 \Sigma_{\mathbf{n}\mathbf{n}'} d\Omega' \quad (48)$$

where $\mathbf{n} = \mathbf{k}/k$, $\mathbf{n}' = \mathbf{k}'/k'$,

$$\Sigma_{\mathbf{n}\mathbf{n}'} = \frac{V}{12m^2 s^4} \sum_{\mu\nu} \left\{ \sum_{\mathbf{R}\mathbf{R}'} \mathbf{nR} \Lambda_{\mathbf{R}\mathbf{R}'}^{\mu\nu} \mathbf{n}'\mathbf{R}' \right\}^2.$$

Note, that the averaged value of the sound velocity $s = (s_l^{-4} + 2s_\perp^{-4})^{-1/4}$ does not coincide with the Debye velocity, even if does not differ significantly.

Any further application of the formula (48) requires some model assumptions regarding the matrix components $\Lambda_{\mathbf{R}\mathbf{R}'}^{\mu\nu}$. They have to obey, however, some relations that follow from the behaviour of the forces in a crystal lattice [36]. In the nearest neighbour approximation this allows to express all matrix elements by one of them (e.g. Λ_{00}) [1]. In case of a vacancy in a simple cubic lattice $\Lambda_{00} = -6ms^2/a^2$ and no free parameters are required. In this case $V = a^3$, $\Sigma_{\mathbf{n}\mathbf{n}'} = (\mathbf{n}\mathbf{n}')^2$ and

$$d\sigma_{\mathbf{k}\mathbf{k}'} = \left(\frac{a}{2\pi} \right)^2 (ka)^4 (\mathbf{n}\mathbf{n}')^2 d\Omega'. \quad (49)$$

In case of impurity, this quantity should be multiplied by a factor $\sigma_0 = (\Lambda_{00}^{\text{impurity}}/\Lambda_{00}^{\text{vacancy}})^2$. Note, that during all the consideration we have not supposed the perturbation caused by the defect small. This is the advantage of the Lifshitz method used. Let us call attention to the following peculiarities when considering isotope defects. In a classical crystal isotope defects interact with the host atoms in approximately the same way and the main difference consists in their mass. This leads to a correction factor $\sigma_0 = (1 - m_{\text{host}}/m_{\text{isotope}})^2$. For ^3He impurities in solid ^4He $\sigma_0 = 1/9$. In case of quantum crystals isotopes differ not only in mass but also in their zero-point

vibrations affecting in this way the local values of the elasticity module [2]. An attempt to estimate this effect was made by Slusarev et al. [37]. They argued that this effect could be larger than that of the mass-difference and that we had not taken it into account. The later statement is not acceptable as seen by the consideration above. In our short letter [17] the principal value of the cross-section (given by the mass-difference) was used in order to avoid model considerations. We shall not discuss here the model assumptions in [37] in detail. However, the correction proposed is given by the quantity $\tilde{\alpha} \approx \Theta_3/\Theta - 1 \approx 0.23$ in the expression (cf. Eq.(15) in Ref.[37])

$$G_1/4 = \alpha^2 + \tilde{\alpha}^2 - \frac{1}{2}\alpha\tilde{\alpha} \approx 0.11 + 0.0145 \quad (50)$$

with $\alpha = \sigma_0 = 1/3$. Obviously, the correction 0.0145 could not be considered as 'larger' than 0.11. In our opinion next terms in Eq.(14) in [37] of the order of $G_1/2^{12} \sim 2 \times 10^{-4}G_1$ are far from the model accuracy used.

The diffusion coefficient may be calculated solving the Boltzmann equation, which is of the type of Fokker-Plank equation [2, 3]. However, the specific features of the defecton motion in the phonon gas allows to solve the problem without resorting to the kinetic equation. We follow here the method proposed in [1, 18].

Since the defecton velocity is much smaller than the sound one the main contribution is due to two-phonon processes. The energy and quasimomentum conservation laws for an individual collision are:

$$\epsilon(\mathbf{p}) + \hbar sk = \epsilon(\mathbf{p}') + \hbar sk' \quad (51)$$

$$\mathbf{p} + \mathbf{k} = \mathbf{p}' + \mathbf{k}' + 2\pi\mathbf{b} \quad (52)$$

where $\mathbf{k}$ and $\mathbf{k}'$ are the quasiwave vectors of the incident and scattered phonons respectively, $\epsilon(\mathbf{p})$ – the defecton dispersion law, and $\mathbf{b}$ is an arbitrary vector of the reciprocal lattice. The linear dispersion law for the phonons is used since the temperature is much smaller than the Debye one. The phonon gas can be considered as in equilibrium, and hence the mean value of the phonon quasimomentum is $\hbar k \propto T/s$. Only phonons with quasiwave vectors near the centre of the Brillouin zone take part in collisions, and Umklapp processes may be neglected. The temperature, in general, can be higher or lower than the defecton band width Δ . In both cases the relative variation of the defecton energy and quasimomentum in a collision are small. If $\Delta \ll T \ll \theta_p$ then Eqs. (51) and (52) yield

$$\delta\epsilon = \frac{\partial\epsilon}{\partial\mathbf{p}}\delta\mathbf{p} = \hbar\mathbf{v}(\mathbf{p} - \mathbf{p}') = \hbar\mathbf{v}(\mathbf{k} - \mathbf{k}') \leq 2v\hbar k \propto 2vT/s$$

and hence,

$$\delta\epsilon/\Delta \leq T/\theta_p \ll 1 \quad (53)$$

In the same way

$$\frac{|\mathbf{p} - \mathbf{p}'|}{p} = \frac{|\mathbf{k} - \mathbf{k}'|}{p} \leq \frac{2T}{\hbar s p} \sim \frac{T}{p a \theta_p} \ll 1, \quad v \propto a \Delta / \hbar \quad (54)$$

In the opposite case, when $T < A < \theta_p$, the defecton dispersion law may be replaced by a quadratic one and the effective mass approximation can be used:

$$\epsilon(p) = \frac{\hbar^2 p^2}{2m^*}$$

Then the change of the phonon wave vector is

$$\chi = k' - k = \frac{k}{p_0} \mathbf{p}(\mathbf{n}' - \mathbf{n}) - \frac{k^2}{p_0} (1 - \mathbf{n}\mathbf{n}') \quad (55)$$

where $p_0 = (m^* s) / \hbar = 2\theta_p / (Aa)$ and $\mathbf{n} = \mathbf{k}/k$, $\mathbf{n}' = \mathbf{k}'/k'$ — the directions of the incident and scattered phonons. The wave vector transferred is

$$\mathbf{q} = k(\mathbf{n} - \mathbf{n}') + \chi \mathbf{n}'. \quad (56)$$

The relative variations of energy and quasimomentum are, therefore, small in this case too

$$\frac{\delta E}{\epsilon(p)} \propto \frac{k}{p} \propto \frac{(AT)^{1/2}}{\theta_p} \ll 1, \quad \frac{q}{p} \propto \frac{k}{p} \ll 1.$$

As for the phonon quasimomentum, its direction changes greatly in each collision, but its magnitude remains practically constant. The situation thus recalls the motion of a heavy particle in a gas of light particles. The difference lies in the dispersion laws and in the different statistics obeyed by the defectons and phonons. It is important also that the width of the defecton energy band is relatively small.

Let us find first the diffusion coefficient in momentum space. Obviously, the change of the square of the wave vector per unit time is given by the integral

$$\langle q^2 \rangle = \frac{3s}{(2\pi)^3 a^5} \int d^3 k d\sigma_{\mathbf{k}\mathbf{k}'} n(k) (\mathbf{k} - \mathbf{k}')^2 \quad (57)$$

where $n(k) = \{\exp(\hbar s k / T) - 1\}^{-1}$ is the phonon distribution function, and $d\sigma_{\mathbf{k}\mathbf{k}'}$ is the differential cross section (48). At low temperatures ($T \ll \theta_p$) the integral in Eq. (57) may be expressed in terms of the Riemann ζ -function:

$$\langle q^2 \rangle = \alpha \frac{\sigma_0 s}{a^3} \left(\frac{T}{\theta_p} \right)^9, \quad \alpha = \frac{\pi^5 \zeta(9)}{240 \zeta(8)} \approx 1, 27. \quad (58)$$

To calculate the diffusion coefficient in coordinate space we proceed as follows. We define the free path time of the defecton as a time during which the transferred momentum squared becomes of the order of the square of the initial particle momentum:

$$\tau = \tau_0 \frac{1}{\alpha \sigma_0} \frac{\overline{\epsilon(p)}}{\theta_p} \left(\frac{\theta_p}{T} \right)^9, \quad \tau_0 = \hbar / A \quad (59)$$

Then the mean free path is the path traversed during the time τ :

$$l = \frac{\sqrt{2}}{\alpha} \frac{a}{\sigma_0} \frac{\overline{\epsilon(p)}^{3/2}}{\theta_p \sqrt{A}} \left(\frac{\theta_p}{T} \right)^9, \quad (60)$$

and the diffusion coefficient in the phonon gas is

$$D_T = \frac{as}{3\alpha\sigma_0} \left(\frac{\overline{\epsilon(p)}}{\theta_p} \right)^2 \left(\frac{\theta_p}{T} \right)^9. \quad (61)$$

The presence of the ninth power the temperature has a lucid physical meaning — three degrees are connected with the number of phonons, four with the scattering cross section, and two with the “ineffectiveness” of the collisions (when a heavy particle is scattered by light ones).

It is instructive to note once again that in all the equations the characteristic temperature parameter is not the Debye temperature Θ as assumed in [6, 11, 13, 32] but $\theta_p \approx \Theta/8$. The effect of this is that the kinetic characteristics evaluated in the works mentioned differ from our results by a great factor of the order of 10^8 .

The mean value $\overline{\epsilon(p)}$ depends both on the temperature region and on the quasiparticle statistics. For Fermi-Dirac statistics, $\overline{\epsilon(p)} = \epsilon_F \propto \Delta x^{2/3}$, and

$$D_F \propto \frac{as}{\sigma_0} x^{4/3} \left(\frac{\Delta}{\theta_p} \right)^2 \left(\frac{\theta_p}{T} \right)^9. \quad (62)$$

In the case of Bose-Einstein statistics:

$$D_B \propto \frac{as}{\sigma_0} \left(\frac{\theta_p}{T} \right)^7. \quad (63)$$

Since the degeneracy temperature $T_0 \propto A x^{2/3}$ is extremely small, the inequality $T_0 \ll T$ is practically satisfied in the whole experimentally accessible region. If at the same time $T < \Delta$, then Boltzmann statistics applies and the relation $\overline{\epsilon(p)} = 3T/2$ may be used to estimate the averages over the temperature. In this case we obtain for the free path time and for the diffusion coefficient, respectively,

$$\tau_B \approx 1, 18 \frac{\tau_0}{\sigma_0} \left(\frac{\theta_p}{T} \right)^8, \quad D_B \approx 0, 59 \frac{as}{\sigma_0} \left(\frac{\theta_p}{T} \right)^7. \quad (64)$$

From the last expression and the Einstein relation we easily obtain the mobility b of the defecton in the phonon gas

$$b = \frac{D_B}{T} = 1, 18 \frac{a^2}{\hbar \sigma_0} \left(\frac{\theta_p}{T} \right)^8. \quad (65)$$

Naturally, the same value of the mobility can be obtained by direct calculation of the force experienced by a quasiparticle moving in the gas. Indeed, in the system in which

the defecton is at rest, the phonon distribution function takes the form $n(\mathbf{k}) = \tilde{n}(\varepsilon - \hbar\mathbf{k}\mathbf{v})$, and the force acting on the defecton can be expressed as the change of momentum per unit time:

$$\mathbf{F} = \frac{3s\hbar}{(2\pi)^3} \int d^3k d\sigma_{\mathbf{k}\mathbf{k}'} \tilde{n}(k) k(\mathbf{n} - \mathbf{n}') = b^{-1}\mathbf{v}.$$

In first order in the small ratio $v/s \ll 1$, the mobility calculated in this manner coincides with that of Eq. (65).

If $T > \Delta$, then the band is filled uniformly and $\epsilon(p) = \Delta$. In this region which is the most interesting one from the experimental point of view we have

$$\tau = \frac{\tau_0}{\alpha\sigma_0} \frac{\Delta}{\theta_p} \left(\frac{\theta_p}{T}\right)^9, \quad D_T = \frac{as}{3\alpha\sigma_0} \left(\frac{\Delta}{\theta_p}\right)^2 \left(\frac{\theta_p}{T}\right)^9. \quad (66)$$

It follows from the deduction made that the results obtained are valid as far as the mean free path l is much longer than the lattice constant ($l \gg a$). This condition leads to the inequality $T < T_k$, where

$$T_k = \theta_p \left(\frac{\sqrt{2z}\Delta}{\alpha\sigma_0\theta_p}\right)^{1/9}. \quad (67)$$

At temperatures $T > T_k$ the mean free path becomes smaller than the interatomic distances, and the free path time τ gets shorter than the delocalization time (7). As a result, the defecton spends a greater part of the time within the cell, and only rarely does it execute individual transitions (tunnel or activation) to a neighbouring equivalent position — the so called *phonon stimulated localization* takes place. At $T = T_k$ the diffusion coefficient is

$$D \propto \frac{a^2\Delta}{\hbar} \quad (68)$$

Its behaviour at higher temperatures calls for a special analysis.

It has been reported in [38] that in a case of light interstitials the law $D \sim T^{-9}$ is valid up to the Debye temperature, independently of the small mean free path. Unfortunately, the melting point of solid helium is much lower the Debye temperature, and hence this prediction cannot be tested experimentally. On the other hand the consideration made in [38] does not take into account that the activation mechanism may become essential far below the Debye temperature Θ .

VI. COMPARISON WITH EXPERIMENT. DETERMINATION OF THE IMPURITON CHARACTERISTICS.

Let us summarize the results obtained and compare them with the available experimental data on diffusion of He impurities in solid He.

The most important processes which determine quantum diffusion in helium are: i) scattering by defects, leading to a temperature independent diffusion, and ii) defecton-phonon scattering which determine the temperature dependence. In the most interesting case when $T \gg \Delta$ the diffusion coefficient is given by Eq. (66). As far as the defecton-defecton and defecton-phonon scattering are independent, the total diffusion coefficient may be obtained using the Matthiessen rule. This yields [17]:

$$D^{-1} = D_0^{-1} + D_T^{-1} = \frac{\theta_p}{as\Delta} \left[2\sqrt{z}x\sigma + 3\alpha\sigma_0 \frac{\theta_p}{\Delta} \left(\frac{T}{\theta_p}\right)^9 \right]. \quad (69)$$

The transition from the temperature regime (66) to the constant value (39) takes place at the temperature

$$T^* = T_k l^{-1/9} \quad (70)$$

where T_k is given by the expression (67). In that way the temperature interval may be divided into three parts. The region $\Delta < T < T^*$ corresponds to impuriton-impuriton scattering while scattering by phonons prevails at $T^* < T < T_k$. At $T > T_k$ (but below the melting point) the classical activation diffusion comes into effect. The diffusion coefficient behaviour is schematically shown in Fig. 2. The diffusion coefficient first decreases exponentially with decreasing temperature to T_k , then increases rapidly ($\sim T^{-9}$), and when $T < T^*$ goes to a plateau which depends on the concentration (to be more precise, on the mean free path $l \sim 1/(x\sigma)$). If $x\sigma \rightarrow 1$, then the mean free path $l \rightarrow 1$, and $T^* \rightarrow T_k$. It is seen, therefore, that the observation of the temperature dependence of the coherent quantum diffusion is possible as far as the coherency condition $l \gg 1$ is fulfilled.

Let us consider for definiteness the case of h.c.p. ⁴He crystal with molar volume $V_m \approx 21 \text{ cm}^3$. Then the values of the quantities included in the expression (69) which can be measured independently are as follows

$$\theta = 26 \text{ K}, \quad \theta_p = 10/3 \text{ K}, \quad a = 3,27 \text{ \AA}, \quad s = 320 \text{ m/s}. \quad (71)$$

The quantity σ_0 calculated with an account of the mass difference of helium isotopes is equal to [17] $\sigma_0 = ((m_4 - m_3)/m_3)^2 = 1/9$. We shall limit ourselves with this value because an account of the change of the elastic moduli [37] would be based on model considerations and would finally give a correction small compared to the experimental error.

Substituting (71) into (69) yields the following expression for the dependence of the diffusion coefficient on the temperature and concentration.

$$D^{-1} = 5.6 \times 10^4 \frac{x\sigma}{\Delta} + \frac{0.1}{\Delta^2} T^9. \quad (72)$$

The expressions for characteristic temperatures then take the form:

$$T_k = 4.2\Delta^{1/9}, \quad T^* = T_k l^{-1/9} \approx T_k (x\sigma)^{1/9} \quad (73)$$

TABLE I: Quantities B , G (74) and σ as functions of the molar volume V_m and concentration x .

x %	V_m cm^3	$B \cdot 10^{11}$ cm^2/s	$G \cdot 10^{-8}$ $\text{cm}^2 \text{s}^{-1} \text{K}^{-9}$	σ	source
0.05	20.23	0.35	4.8	173	[27]
0.05	20.42	0.45	7.7	162	[27]
0.05	20.62	0.9	4.5	104	[27]
0.05	20.84	1.6	10	71	[27]
0.05	20.98	2.8	10	48	[27]
0.01	20.95	2.32			[39]
0.01	21	2.8	10		[27]
0.02	21	2.8	10		[27]
0.0242	20.95	2.35			[39]
0.0499	20.95	1.9			[39]
0.05	21		24		[40]
0.006	20.95	1.0	24		[41]
0.12	21		24		[40]
0.25	21	0.81			[14]
0.01	20.70	1.1			[39]
0.242	20.70	1.2			[39]
0.0499	20.70	0.9			[39]

The second term in (72) corresponding to the diffusion law (66) allows to determine the band width Δ *from the temperature dependence only*. Having the value of Δ one can calculate the cross-section σ from the first addend.

In order to study the dependence on the molar volume V_m let us write the expression (69) in the form:

$$D^{-1} = B^{-1}x + G^{-1}T^9 \quad (74)$$

where

$$B = D_0 x, \quad G = 2.4 a s \Delta^2 \theta_p^7 = 4.8 \frac{a^2}{\hbar} \Delta^2 \theta_p^8. \quad (75)$$

The values of the coefficients B and G at different molar volumes and concentrations are given in Table 1. As far as the dependence of θ_p on V_m is known (the Grüneisen parameter γ is the same as for the Debye temperature). Eq. (11) enables us to find the "Grüneisen parameter for the band width" γ_Δ :

$$\gamma_\Delta = d(\ln \Delta)/d(\ln V_m) = 4\gamma - \frac{1}{3} + \frac{1}{2}\gamma_G \quad (76)$$

where

$$\gamma_G = d(\ln G)/d(\ln V_m).$$

Substituting here $\gamma = 2, 6$ and calculating $\gamma_G \approx 21$ from the experimental data given in Table 1 yield $\gamma_\Delta \approx 21$.

This value is close to that for the Grüneisen parameter for the exchange integral in ^3He ($\gamma_j \approx 18$). Unfortunately, the experiment is not precise enough to lead to unique conclusions.

Let us turn now to Eq. (40) and write the Grüneisen parameter in the form

$$\Gamma = \partial(\ln D)/\partial(\ln V_m) = 2\gamma_\Delta - \gamma_{v_0} + \frac{2}{3} \approx 42\frac{2}{3} - \gamma_{v_0}. \quad (77)$$

The experimental values of Γ differs significantly even within the publications of one and the same group. In [14] the value

$$\Gamma = 47 \pm 11, \quad (78)$$

has been obtained while Allen, Richards and Schratter [27, 39, 42] reported

$$\Gamma = 57 \pm 12. \quad (79)$$

A conclusion may be made from a comparison of (70) and (71) that the interaction between impurities (characterized by the quantity V_0) depends on the molar volume relatively small: $\gamma_v \approx 5$. Such a dependence can be obtained assuming that $V_0 \sim K_T a^3$, where K_T is the isothermal modulus of elasticity [40]. On the other hand a comparison of (70) and (72) leads to a strong dependence: $\gamma_v \approx 16$.

Let us show now the order of calculation of defecton characteristics on the bases of the data in Table 1. Estimation will be made for $V_m = 21 \text{ cm}^3$, $x = 0.05\%$, $B = 2.8 \times 10^{-11}$ [27]. Comparing the values for G with Eq. (72) yields the band width $\Delta = 10^{-4} \text{ K}$. Substituting the result obtained into the expression for B (the first term in (72)) at given concentration one obtains the cross-section $\sigma = 10^4 \Delta / (5, 6B) = 64 a^2$. Then V_0 may be obtained from (24): $V_0 \sim \sigma \Delta \sim 0, 65 \times 10^{-2} \text{ K}$ (Eq. (21) gives slightly larger value of the same order.) Making use of (35) one may calculate the mean free path $l = a/(\sqrt{2}x\sigma) \approx 23 a$ and verify the coherency condition $l \gg a$. Finally, temperatures T_k and T^* are calculated and compared with the experimental curve $D(T)$. This procedure yields:

$$\Delta \approx 10^{-4} \text{ K}, \quad \sigma \sim 64 a^2, \quad V_0 \sim 10^{-2} \text{ K}$$

$$T_k = 1.2 \text{ K}, \quad T^* = 0.7(10^4 x)^{1/9} \text{ K}. \quad (80)$$

If the value $G = 2.4 \times 10^7$ reported in Refs. 40, 41 is used, then $\Delta \approx 1.5 \times 10^{-4} \text{ K}$. Both values are within the experimental error.

In regard to the concentration regions one obtains that the gas approximation is valid at concentrations

$$x < \sigma^{-3/2} \approx 10^{-3}, \quad (81)$$

and the region of interacting quasiparticles is given by the inequalities

$$10^{-3} < x < 10^{-2}. \quad (82)$$

A comparison of theoretical and experimental results [27, 40, 41] is shown in Figs. 3, 4, ??, 5, 6, 7. Fig. 3 is an experimental corroboration of the ninth degree in the diffusion law (66), Fig. 4 shows the concentration dependence of the diffusion coefficient in the region of the

low-temperature plateau. The temperature dependencies at different concentrations and molar volumes are shown in Fig. ?? and Figs. 5, 6, 7.

In order to avoid any misunderstanding it is worth nothing that an interpolation formula analogous to (69) has been used also in [7, 14, 22, 43]:

$$D^{-1} = \frac{\hbar}{Aa^2} \left[x + \frac{\theta}{A} \left(\frac{T}{\Theta} \right)^9 \right]. \quad (83)$$

This expression contains two essential differences compared to (69). The first one is the presence of the Debye temperature $\Theta \approx 8\theta_p$ instead of θ_p . The second one is that (83) does not contain the cross-section σ which role has already been considered. The same error is present also in [20, 44]. That is why the values of the band width obtained in these works turned out to be smaller by more than 2 orders of magnitude.

In order to describe the temperature dependence in the third region in Fig. 2 one has to add the classical expression

$$D_v = \frac{a^2}{6} \omega_v \exp\{-\Phi_v/T\} \quad (84)$$

where the subscript v refers to vacancies because the diffusion is dominated by the vacancy-impurity exchange. Typical values of the exchange frequency is $\omega_v \sim 10^8 \div 10^9 \text{ s}^{-1} \sim 10^{-2} \text{ K}$. The final form of the diffusion coefficient is therefore:

$$D_{tot} = D + D_v = \left\{ C_1 \frac{x\sigma}{\Delta} + C_2 \frac{\theta_p^2}{\Delta^2} \left(\frac{T}{\theta_p} \right)^9 \right\}^{-1} + D_v^0 e^{-\Phi_v/T} \quad (85)$$

where D is given by eq. (69), and

$$C_1 = \frac{\hbar\sqrt{z}}{k_B a^2} \approx (2.5 \pm 0.5) \times 10^4 \text{ K.s/cm}^2, \quad (86)$$

$$C_2 = \frac{3\alpha\sigma_0}{as} = (440 \pm 15) \text{ cm}^{-2}\text{s}, \quad (87)$$

$$D_v^0 = \frac{1}{6} a^2 \omega_v = (3 \div 10) \times 10^{-7} \text{ cm}^2/\text{s} \quad (88)$$

with k_B – the Boltzmann constant. The quantities θ_p and Δ depend on the molar volume. The Grüneisen parameter for θ_p is the same as for Θ_D . According to Edwards and Pandorf [45] for ^4He $\Theta_D = 7.12 \times 10^4 / V_m^{2.60} \text{ K}$. For θ_p one has

$$\theta_p = 0.91 \times 10^4 V_m^{-2.60} \text{ K}. \quad (89)$$

We plot in Fig. 5, Fig. 6 and Fig. 7 the dependencies (69) and (85). The quantity θ_p is calculated using (89). The experimental points are from Ref. 27. The fit may

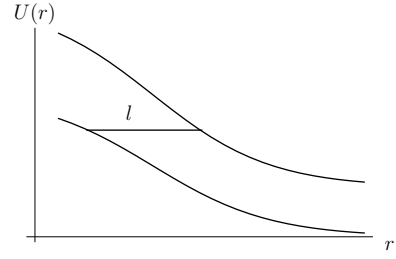


FIG. 1: Defecton band shape in the deformation field. The mean free path l is determined by the scattering on the defecton band boundaries.

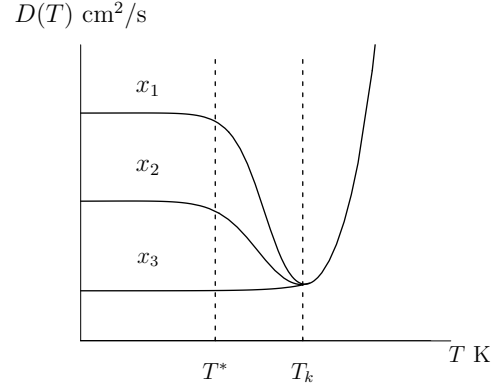


FIG. 2: Schematic representation of the diffusion coefficient for $x_3 < x_2 < x_1$.

be improved by further variation of the parameters, but this seems not reasonable having in mind the approximations made. It is seen that the activation energy Φ is in good agreement with what has been observed experimentally [27] and increases with decreasing molar volume as it should. The band width also manifests a strong molar dependence changing almost two times from $V_m = 21 \text{ cm}^3$ to $V_m = 20.60 \text{ cm}^3$. The corresponding Grüneisen parameter is approximately 25 in good agreement with eq. (76).

VII. PHONON-CONTROLLED VERSUS VACANCY-CONTROLLED DIFFUSION

Although the theory of quantum diffusion has been well confirmed by the experiment some attempts to regenerate the idea of thermal vacancy-assisted diffusion have appeared recently [46, 47, 48, 49, 50]. This mechanism was proposed by Locke [51]. The diffusion coefficient in case of vacancy-impurity scattering is of the form (11) with $A = J_{34}^2 / \omega_v$:

$$D_{IV} = \frac{\pi}{4} \frac{k_B J_{34}^2 a^2}{\hbar \omega_v x_v \sigma_{IV}} \quad (90)$$

where ω_v is the ^4He -vacancy exchange rate, x_v is the vacancy concentration, and σ_{IV} is the impurity-vacancy

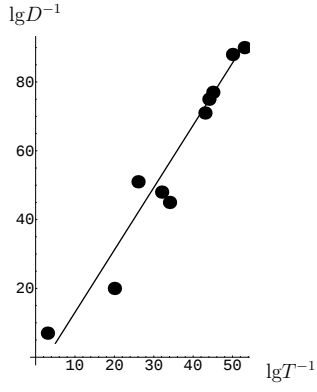


FIG. 3: The dependence of the diffusion coefficient on the temperature. The straight line correspond to the law $\lg D^{-1} = 9 \lg T + 6.613$.

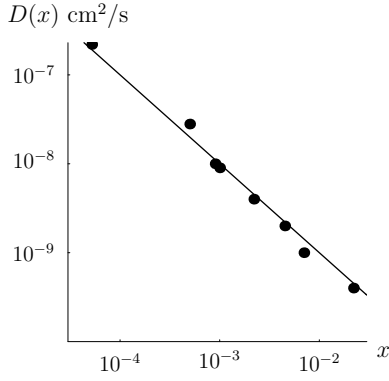


FIG. 4: Concentration dependence of the diffusion coefficient at $V_m = 20.95 \text{ cm}^3$ in the region of the low-temperature plateau after [41].

cross-section (in units a^2). Since the vacancy concentration increases with increasing temperature as $x_v \sim e^{-\Phi/T}$, the diffusion coefficient varies exponentially and increases with decreasing temperature as

$$D_{IV} = D_{IV}^0 e^{\Phi/T} \quad (91)$$

with

$$D_{IV}^0 = \frac{\pi k_B J_{34}^2 a^2}{4 \hbar \omega_v \sigma_{IV}} = 1.77 \times 10^{-14} \text{ cm}^2/\text{s} \quad (92)$$

where the following values of parameters were used in Ref. 51:

$$\begin{aligned} \Phi &= 12 \text{ K}, \quad a = 3.67 \text{ \AA}, \quad \omega_v = 0.02 \text{ K}, \\ J_{34} &= 8 \times 10^{-7} \text{ K}, \quad \sigma_{IV} = 0.25 \end{aligned} \quad (93)$$

The fit was found not satisfactory (see Ref. [27, 51]).

Kisvarsanyi and Sullivan (KS) [48] used the same formula with higher values of J_{34}

$$J_{34}/2\pi = 2.3 \times 10^5 \text{ Hz, i.e. } J_{34} = 1.1 \times 10^{-5} \text{ K} \quad (94)$$

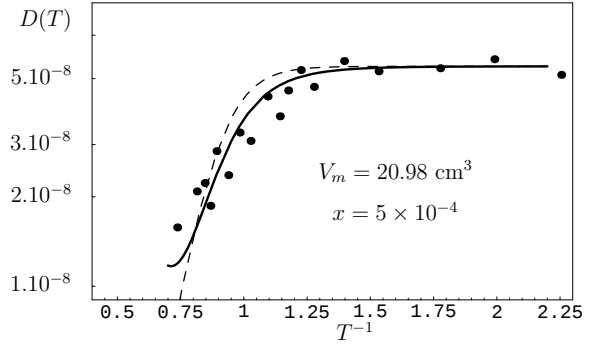


FIG. 5: Temperature dependence of the diffusion coefficient at fixed concentration $x = 5.10^{-4}$ and a molar volumes $V_m = 20.98 \text{ cm}^3$. Experimental points from Ref. 27. Solid line: theoretical curve (69) for $\theta_p = 3.33 \text{ K}$, $\Delta = 0.9 \times 10^{-4} \text{ K}$, $D_0 = 5.5 \times 10^{-8} \text{ cm}^2/\text{s}$, $\omega_v = 3 \times 10^9 \text{ s}^{-1}$ [27], $\Phi = 7.1 \text{ K}$; dashed line corresponds to Eq. (98), $\Phi = 11.5 \text{ K}$, $\omega_v = 1.2 \times 10^9 \text{ s}^{-1}$.

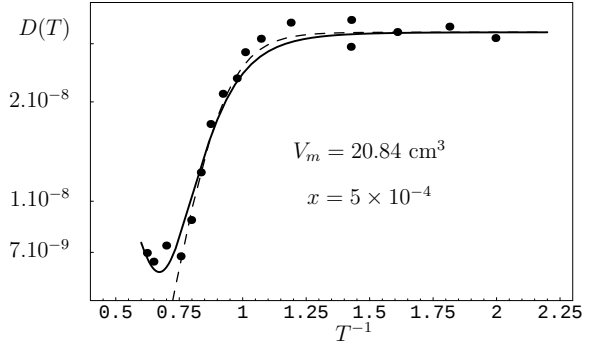


FIG. 6: Temperature dependence of the diffusion coefficient at fixed concentration $x = 5.10^{-4}$ and a molar volumes $V_m = 20.84 \text{ cm}^3$. Experimental points from Ref. 27. Solid line: theoretical curve (69) for $\theta_p = 3.39 \text{ K}$, $\Delta = 0.9 \times 10^{-4} \text{ K}$, $\Phi = 8 \text{ K}$; dashed line – Eq. (98) with the same parameters as in Fig. 5 but $\Phi = 11 \text{ K}$.

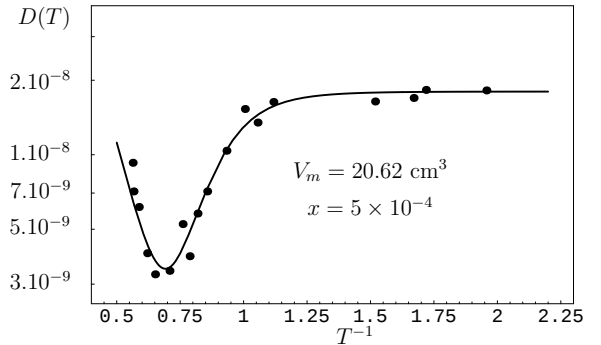


FIG. 7: Temperature dependence of the diffusion coefficient at fixed concentration $x = 5.10^{-4}$ and a molar volumes $V_m = 20.62 \text{ cm}^3$. Experimental points from Ref. 27. Solid line: theoretical curve (85) with $\Phi = 9 \text{ K}$, $D_0 = 1.8 \times 10^{-8}$ [27], $\theta_p = 3.47 \text{ K}$ (89), $\Delta = 0.6 \times 10^{-4} \text{ K}$.

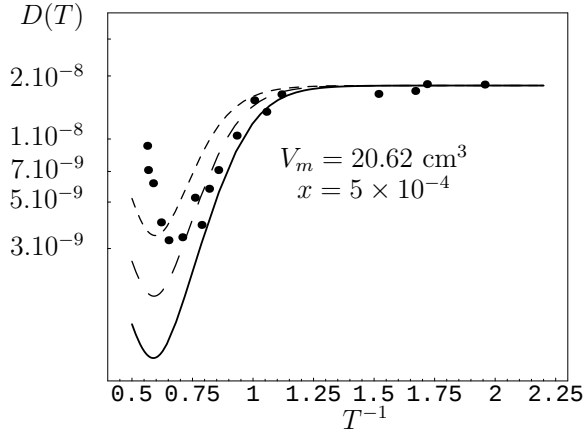


FIG. 8: The diffusion coefficient (98) for fixed $\Phi = 10.5$ K and different values of ω : solid line: $\omega = 1.2 \times 10^9$ s $^{-1}$; long dash line: $\omega = 2.4 \times 10^9$ s $^{-1}$; short dash line: $\omega = 4.8 \times 10^9$ s $^{-1}$

and slightly different values of the other parameters, namely:

$$\sigma_{IV} = 1.40, \quad \omega_v = 1.2 \times 10^9 \text{ s}^{-1} = 0.93 \times 10^{-2} \text{ K} \quad (95)$$

With $a = 3.27 \times 10^{-8}$ cm this yields:

$$D_{IV}^{KS} = 1.03 \times 10^{-12} e^{\Phi/T} \text{ cm}^2/\text{s} \quad (96)$$

Hence, one has for the diffusion coefficient

$$(D^{KS})^{-1} = D_0^{-1} + (D_{IV}^{KS})^{-1} \quad (97)$$

instead of (69). The diffusion coefficient for the whole temperature region (85) is then replaced by

$$D_{tot}^{KS} = (D_0^{-1} + (D_{IV}^{KS})^{-1})^{-1} + D_v \quad (98)$$

with D_v from (84).

In their works Kisvarsanyi and Sullivan [48] (see also Refs. 49, 50) argue that eq. (98) describes well the experimental data of Allen, Richards and Schratter [27] and that "the overall fit for only one adjustable parameter is very good". The value of this parameter for $V_m = 20.62$ cm 3 and $x = 5 \times 10^{-4}$ was found to be $\Phi = 10.5$ K. We check this in Fig. 8 (solid line). For comparison we show the function (98) for different values of ω . Unfortunately, we do not see any satisfactory agreement. Farther on, it is confusing that in KS theory the vacancy activation energy Φ decreases with decreasing molar volume ($\Phi = 11.5$ K at $V_m = 21$ cm 3 , and $\Phi = 10.5$ K at $V_m = 20.62$ cm 3). Some other comments on their theory can be found in Refs. 52, 53. However, there are two points we have to discuss here. One is concerning the impurity-vacancy cross-section $\sigma_{IV} = 1.40$ a 2 . There are no details about its calculation. The only available information is that "the standard central force approach as given by Goldstein [54]" and Lennard-Jones 6-12 potential have been used. Following the reference link one

sees that one of the authors cites a private communication to herself [46]. This important point, therefore, needs elucidation.

The second point concerns neglecting of the impuriton-phonon scattering leading to $D_T = G^{-1}T^{-9}$ (cf. Eqs. (66), (74), (75)). KS have compared the reciprocal values of the diffusion coefficients given by expressions (66) and (91) and have come to the conclusion that the impuriton-phonon scattering is weaker by more than two orders. As a result, they have neglected D_T . However, as it was shown in [53], they have made a plain arithmetical mistake when evaluating the factor G . Indeed, they have written the factor G in the form

$$G_{KS}^{-1} = \frac{5z}{32\pi^9} (6\pi^2)^{-2/3} \frac{a^2 J_{34}^2}{\omega_D} \Theta_D^9 = 4.14 \times 10^{-6} \frac{a^2 J_{34}^2}{\omega_D} \Theta_D^9 \quad (99)$$

and have used the following set of parameters

$$\Theta_D = 30 \text{ K}, \quad \omega_D = k_B \Theta_D / \hbar = 3.9 \times 10^{12} \text{ s}^{-1},$$

$$J_{34} = 2\pi \times 2.3 \times 10^5 = 1.44 \times 10^6 \text{ s}^{-1}$$

Substituting into (99) yields

$$G_{KS}^{-1} = 0.45 \times 10^{-7} \text{ cm}^2 \text{ s}^{-1} \text{ K}^9, \quad G_{KS} = 2.2 \times 10^7 \quad (100)$$

in perfect agreement with the values used in our works and confirmed by the experiment. KS have calculated $G_{KS}^{-1} = 6.0 \times 10^{-5}$, i.e. more than 10^3 times larger. As a result, they have neglected the larger term, not the smaller.

In their Reply [50] to the Comment [53], KS have made an attempt to justify themselves by an inappropriate variation of the set of parameters. They changed Θ_D from 30 K to 33 K (this Debye temperature corresponds to $V_m = 19.18$ cm 3 far away from the region considered; in fact $\Theta_D = 26$ K for $V_m = 21$ cm 3 [45]), and J_{34} from 1.5×10^6 s $^{-1}$ to 15.7×10^6 s $^{-1} = 1.2 \times 10^{-4}$ K (a value more than 10 times larger than the experimental one). But even with these unrealistic values they were not able to reach 6.0×10^{-5} K.

VIII. CONCLUSION

We presented in this work the main ideas and results on quantum diffusion of defects in solid helium. We showed that the strong temperature dependence, predicted in [1, 11] can be explained very well by the phonon-defecton scattering. The interpolation formula (85) is in the excellent agreement with the experimental data available. The theory allows evaluation of some important quasiparticle characteristic by direct comparison with the experiment. The exchange integral and defecton band width were estimated. The fundamental role of the narrowness of energy band width in the defecton-defecton scattering and the resulting giant cross-sections predicted in [1, 17] were confirmed. The dependence of the kinetic characteristics

on the molar volume was analyzed as well. A critical analysis of some other theoretical models and calculations was made. In particular, the inconsistency of the vacancy-assisted diffusion [48] at low temperatures was shown.

Acknowledgments

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- [1] D.I.Pushkarov, *Zh. Eksp. Teor. Fiz.* **59**, 1755 (1970) [*Sov. Phys. JETP* **32**, 954 (1971)]
 - [2] D.I.Pushkarov, *Quasiparticle Theory of Defectons in Solids*, World Scientific (Singapore-New Jersey-London-Hong Kong, (1990)
 - [3] D.I.Pushkarov, *Defektony v kristallah; metod kvazichastich v kvantovoj teorii defektov*, Nauka, Moscow (in Russian)
 - [4] D.I. Pushkarov, *Fiz.Nizk.Temp.* **1** 586 (1975); [*Sov.J.Low.Temp.Phys.* **1**(5) 283-285 (1975)]
 - [5] D.I.Pushkarov and Kh.I.Pushkarov, *Phys. Stat. Sol. (b)* **67** K23 (1975)
 - [6] B.N.Essel'son et al., *Properties of liquid and solid helium. Solutions $^3\text{He} - ^4\text{He}$* , (Naukova Dumka, Kiev, 1982), in Russian
 - [7] B.N.Essel'son et al., *Solutions of quantum liquids* (Nauka, Moscow, 1973), in Russian.
 - [8] I.F.Silvera, *Rev. Mod. Phys.* **B93** 52 (1980)
 - [9] A.Abragam and M.Goldman, *Nuclear Magnetism: Order and Disorder* (Clarendon Press, Oxford, 1982)
 - [10] D.I.Pushkarov, *Phys. Stat. Sol. (b)* **133** 525 (1986)
 - [11] A.F.Andreev and I.M. Lifshitz, *Zh. Eksp. Teor. Fiz.* **56**, 2057 (1969)
 - [12] R.A.Guyer and L.I.Zane, *Phys. Rev. Lett.* **24** 660 (1970)
 - [13] V.N.Grigoriev et al., *Zh. Eksp. Teor. Fiz.* **64**, 608 (1973)
 - [14] V.N.Grigoriev et al., *Zh. Eksp. Teor. Fiz.* **66** 321 (1974) [*Sov.Phys.-JETP* **39**, 153 (1974)]
 - [15] C.P.Flynn and A.M.Stoneham, *Phys. Rev.* **1** 3966 (1970)
 - [16] D.I.Pushkarov, *Quantum Theory of Defects in Crystals at Low Temp.* PhD Thesis, Moscow Univ., Moscow (1972)
 - [17] D.I.Pushkarov, *Pis'ma v Zh. Eksp. Teor. Fiz.* **19**, 751 (1974) [*Sov. Phys. JETP* **19** 386 (1974)]
 - [18] D.I.Pushkarov, *Zh. Eksp. Teor. Fiz.* **68** 1471 (1975) [*Sov.Phys.JETP* **41**, 735 (1976)]
 - [19] D.S.Miyoshi, R.M.Cotts, A.S.Greenberg and R.C.Richardson, *Phys. Rev. A* **2** 870 (1970)
 - [20] R.G.Richards, J.Pope and A.Widom, *Phys. Rev. Lett.* **29**, 708 (1972)
 - [21] V.N.Grigoriev et al., *Pis'ma v Zh. Eksp. Teor. Fiz.* **17**, 25 (1973)
 - [22] V.N.Grigoriev et al., *J. Low Temp. Phys.* **13** 65 (1/2) (1973)
 - [23] A.Landesman and J.M.Winter, in *Low Temperature Physics*, Proc. of LT13, **v.2.**, 73 (Plenum, New York, London, 1974)
 - [24] W.Huang, H.A.Goldberg and R.A.Guyer, *Phys. Rev. B* **11**, 3374 (1975)
 - [25] A.Landesman, *Phys. Lett. A* **54** 137 (1975)
 - [26] Y.Yamashita, *J. Phys. Soc. Japan* **37** 1210 (1974)
 - [27] A.R.Allen, M.G.Richards and J.Schratter, *J. Low Temp Phys.* **47** 289 (1982)
 - [28] V.A.Slusarev et al., *Fiz. Nizkih Temp.* **3** 1229 (1977)
 - [29] D.I.Pushkarov and Kh.I.Pushkarov, *Phys. Stat. Sol. (b)* **74**, K97 (1976)
 - [30] J.E.Sacco, A.Widom, *J.Low Temp. Phys.* **24** 241 (1976)
 - [31] R. Feynman, *The Feynman Lectures on Physics*, Addison-Wesley publ. comp., Massachusetts (1963)-Chpt. 43 "Diffusion".
 - [32] A.F.Andreev, *Usp. Fiz. Nauk* **118**, 251 (1976)
 - [33] I.M.Lifshitz, *Zh. Eksp. Teor. Fiz.* **18** 293 (1948)
 - [34] I.M.Lifshitz, M.I.Kaganov, *Usp. Fiz. Nauk.* **69**, 419 (1959)
 - [35] I.M.Lifshitz, M.Ya.Azbel and M.I.Kaganov, *Electr. Theory of Metals* (Nauka, Moscow, 1971) in Russian.
 - [36] A.A. Maradudin, E.W. Montroll, G.H. Weiss, "Theory of Lattice Dynamics in the Harmonic Approximation", - Acad. Press, New York and London (1963)
 - [37] V.A.Slusarev et al., *Fiz. Nizkih Temp.* **3** 1229 (1977)
 - [38] Yu.Kagan and M.I.Klinger, *J. Phys. C: Solid-State Phys.* **7**, 2791 (1974)
 - [39] J.Schratter and A.R.Allen, *J. Low Temp. Phys.* **57**, 179 (1984)
 - [40] B.N.Essel'son et al., in *Proc. 20-th Soviet Conf. at Low Temp. Phys.* **NT-20**, **2**, 236 (Moscow 1979)
 - [41] B.N.Essel'son et al., *Zh. Eksp. Teor. Fiz.* **74**, 2311 (1978)
 - [42] A.R.Allen, M.G.Richards and J.Schratter, *J.Phys.(Paris)* **39** (Coll.C6), C6-113 (1978)
 - [43] V.N.Grigoriev et al., *Fizika Nizkih Temp.* **1** 5 (1975)
 - [44] A.Widom and M.G.Richards, *Phys. Rev. A* **6** 1196 (1972)
 - [45] D.O. Edwards, R.C. Pandorf, *Phys.Rev.* **140** A 816 (1965)
 - [46] E.G. Kisvarsanyi, K. Runge, N.S. Sullivan, *Phys.Lett. A* **155** 337 (1991)
 - [47] M.Rall, D.Zhou, E.G. Kisvarsanyi, N.S. Sullivan, *Phys.Rev. B* **45** 2800 (1992)
 - [48] E.G. Kisvarsanyi, N.S. Sullivan, *Phys.Rev. B* **48** 16557 (1993)
 - [49] E.G. Kisvarsanyi, N.S. Sullivan, *Phys.Rev. B* **55** 3989 (1997)
 - [50] E.G. Kisvarsanyi, N.S. Sullivan, *Phys.Rev. B* **61** 15476 (2000)
 - [51] D.P. Locke, *J.Low Temp. Phys* **32** 159 (1978)
 - [52] V.N. Grigorev, *Phys.Rev. B* **55** (6) 3987 (1997)
 - [53] D.I. Pushkarov, *Phys.Rev. B* **61** 15474 (2000)
 - [54] H. Goldstein, *Classical Mechanics* (Addison-Wesley, Reading, MA, q980), Chpt. 3 Eq. (397)